

Electronic supplementary information for:

**Photocatalytic hydrogen evolution over nickel cobalt bimetallic
phosphate anchored graphitic carbon nitrides by regulation of d-
band electronic structure**

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Table S1. Summary of non-noble based cocatalysts for photocatalyst hydrogen evolution.

Photocatalyst	cocatalyst	Reaction condition	Light source	H ₂ evolution ($\mu\text{mol h}^{-1}\text{g}^{-1}\text{cat}$)	Ref.
CdS	MoO _x	20 vol% lactic	$\lambda > 400 \text{ nm}$	2868	1
MIL-125-NH ₂	NiO/Ni ₂ P	16 vol% TEA	$\lambda > 420 \text{ nm}$	1084/1230	2
SrTiO ₃	Ni@NiO _x	Pure water	$\lambda > 300 \text{ nm}$	~18	3
g-C ₃ N ₄	Mo-Mo ₂ C	20 vol% TEOA	$\lambda > 420 \text{ nm}$	219.7	4
g-C ₃ N ₄	Ni ₂ P@BP	10 vol% TEOA	$\lambda > 420 \text{ nm}$	858.2	5
g-C ₃ N ₄	Ni-Mo	10 vol% TEOA	$\lambda > 420 \text{ nm}$	1785	6
g-C ₃ N ₄	NiO	10 vol% TEOA	$\lambda > 420 \text{ nm}$	68.8	7
g-C ₃ N ₄	Ni ₂ P	10 vol% TEOA	$\lambda > 420 \text{ nm}$	82.5	8
g-C ₃ N ₄	Ni ₃ C	15 vol% TEOA	$\lambda > 420 \text{ nm}$	303.6	9
g-C ₃ N ₄	CoP	15 vol% TEOA	$\lambda > 420 \text{ nm}$	1924	10
g-C ₃ N ₄	CoS _x	20 vol% TEOA	$\lambda > 400 \text{ nm}$	629	11
sg-CN	Ni ₂ P	10 vol% TEOA	$\lambda > 420 \text{ nm}$	330	12
g-C ₃ N ₄	NiCoP@NiCo-Pi	10 vol% TEOA	$\lambda > 420 \text{ nm}$	534.2	13
g-C ₃ N ₄	NiCo-Pi	10 vol% TEOA	$\lambda = 410 \text{ nm}$	10184	This work

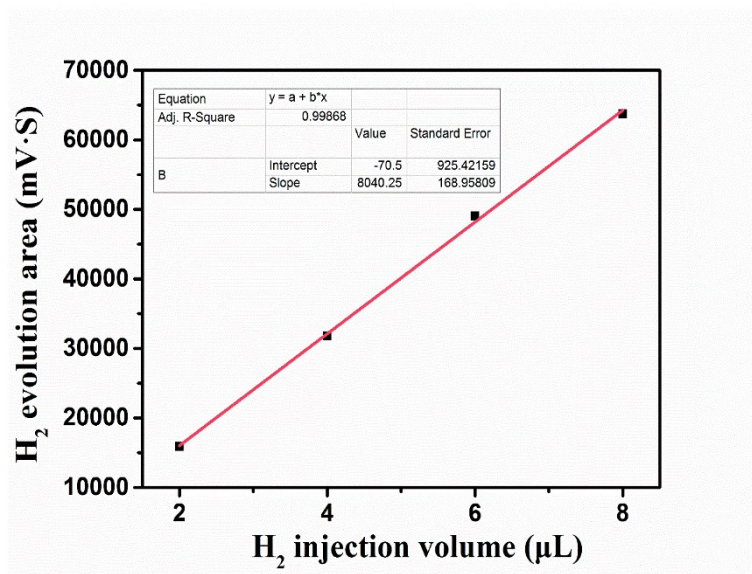


Fig. S1. Standard curve for H₂ established by gas chromatography. The inset shows the corresponding fitting information.

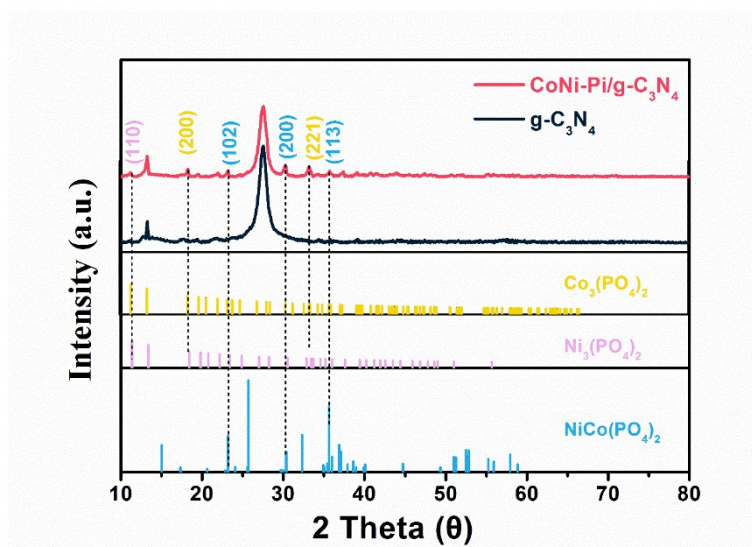


Fig. S2. X-ray diffraction (XRD) patterns of g-C₃N₄ and NiCo-Pi/g-C₃N₄. There are some new diffraction peaks (blue color) on the NiCo-Pi/g-C₃N₄, which can be mainly assigned to CoNi(PO₄)₂, indicating that the formation of NiCo-Pi solid solution. The diffraction peaks (pink and yellow) can be mainly assigned to Co₃(PO₄)₂ (PDF#41-0375) and Ni₃(PO₄)₂ (PDF#33-0951).

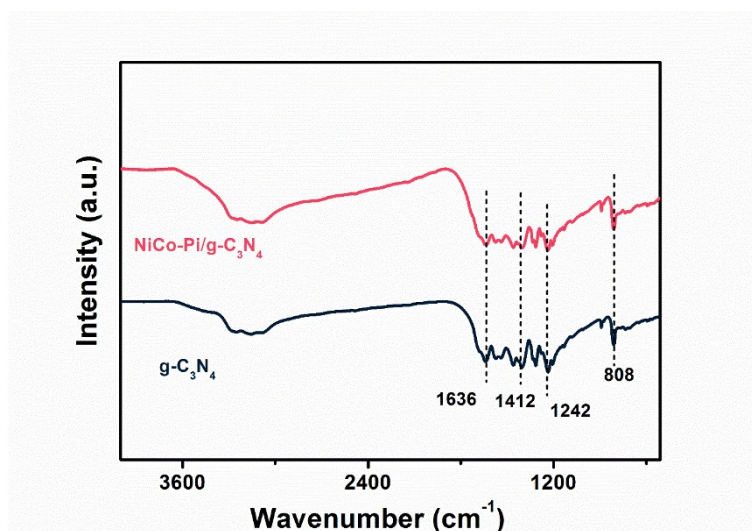


Fig. S3. Fourier transform infrared (FT-IR) spectra of g-C₃N₄ and NiCo-Pi/g-C₃N₄.

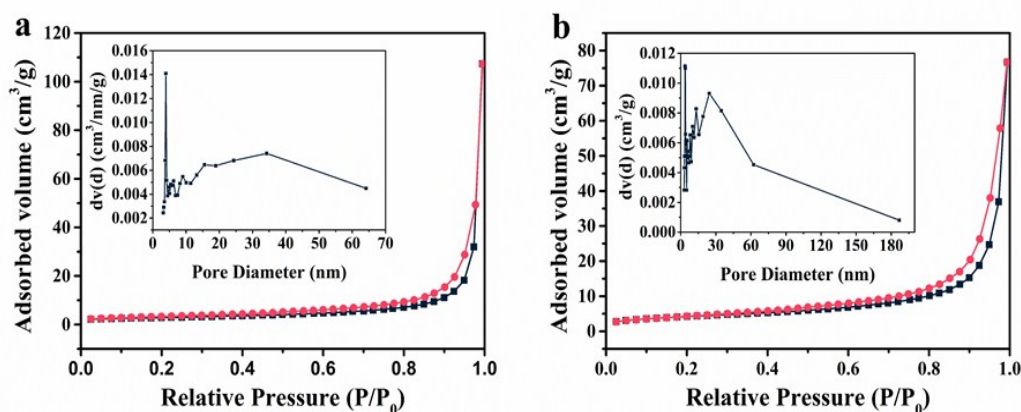


Fig. S4. (a) N₂ adsorption–desorption isotherms and the corresponding pore distribution curves of g-C₃N₄ (inset); (b) N₂ adsorption–desorption isotherms and the corresponding pore distribution curves of NiCo-Pi/g-C₃N₄ (inset).

The Brunauer-Emmett-Teller (BET) surface area and the Barret-Joyner-Halenda (BJH) pore size distribution of the samples were obtained from the N₂ adsorption-desorption measurements. The N₂ adsorption-desorption isotherms of the g-C₃N₄ and NiCo-Pi/g-C₃N₄ samples are type IV with H3-type hysteresis loops ($0.8 < P/P_0 < 1.0$), indicating the presence of mesoporous and macropores.¹⁴ The BET surface area of NiCo-Pi/g-C₃N₄ was calculated to be $79.5 \text{ m}^2 \text{ g}^{-1}$, which is much higher than that of g-C₃N₄ ($57.6 \text{ m}^2 \text{ g}^{-1}$). Additionally, the pore size distribution curve of g-C₃N₄ exhibits a sharp peak at 3.9 nm, while the pore size distribution of NiCo-Pi/g-C₃N₄ is widely distributed between 0-30 nm.

Table S2. Textural properties of the pure g-C₃N₄ and NiCo-Pi/g-C₃N₄ composite.

Sample	Surface area (m ² g ⁻¹)	Pore size (nm)	Pore volume (cm ³ g ⁻¹)
g-C ₃ N ₄	57.6	19.7	0.205
NiCo-Pi/g-C ₃ N ₄	79.5	18.1	0.302

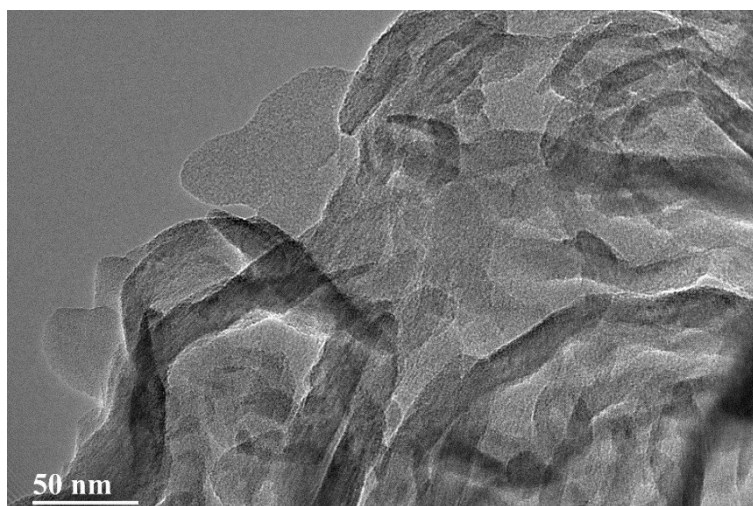


Fig. S5. Transmission electron microscopy (TEM) image of as-prepared g-C₃N₄ with layer by layer structures.

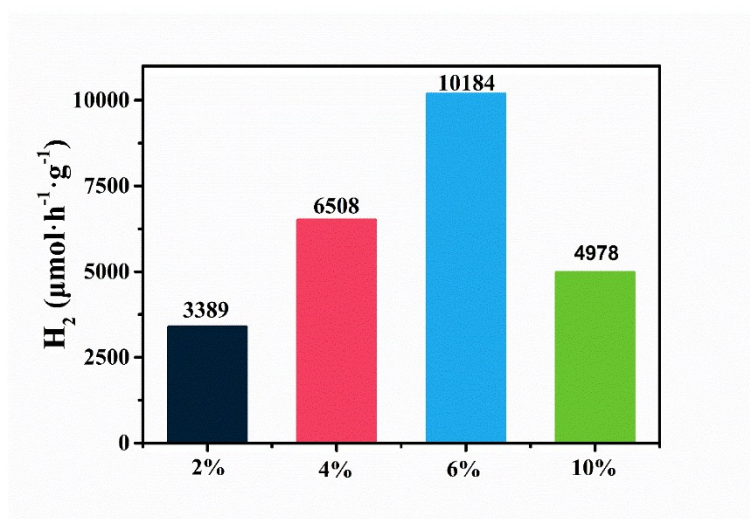


Fig. S6. Photocatalytic H₂ evolution rate of NiCo-Pi/g-C₃N₄ composites (Ni/Co molar ratio of 4:5) with different NiCo-Pi contents (2 wt%, 4 wt%, 6 wt%, 10 wt%) under visible light. The H₂ evolution rate increased from 2 wt% to 6 wt%, and decreased thereafter, probably because the excess of NiCo-Pi resulted in the shielding of the active sites on the catalyst surface and reduced the light penetration depth in the reaction solution.

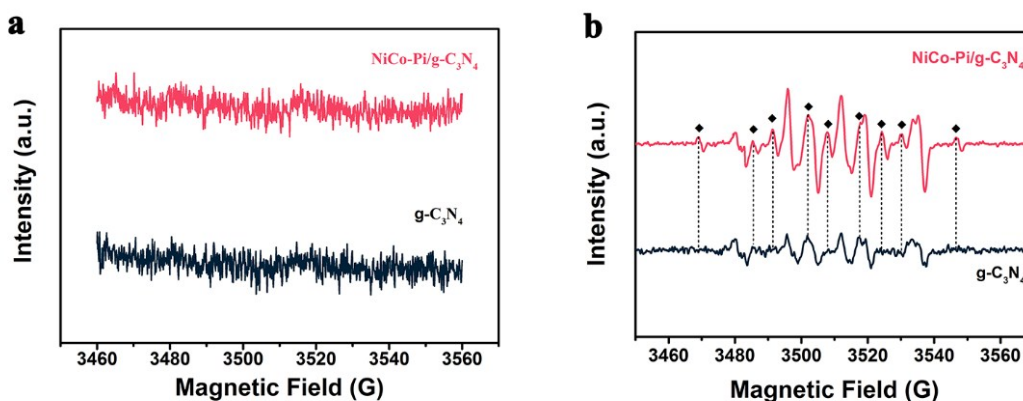


Fig. S7. (a) DMPO adducts recorded in the binary systems containing H₂O and catalyst under visible light ($\lambda \square 420$ nm). (b) DMPO adducts recorded in the ternary systems containing H₂O, TEOA and catalyst (\blacklozenge :- DMPO- \cdot H) under visible light ($\lambda \square 420$ nm). As shown in the Fig. S7a, no free radicals were detected in pure water, indicating that the redox reaction of water would not occur. It is worth noting that hydrogen radicals (\cdot H) are trapped in the presence of sacrificial agents,^{15,16} and the signal strength of NiCo-Pi/g-C₃N₄ is significantly stronger than that of the original g-C₃N₄ (Fig. S7b), which indicates that NiCo-Pi can indeed promote the proton reduction reaction.

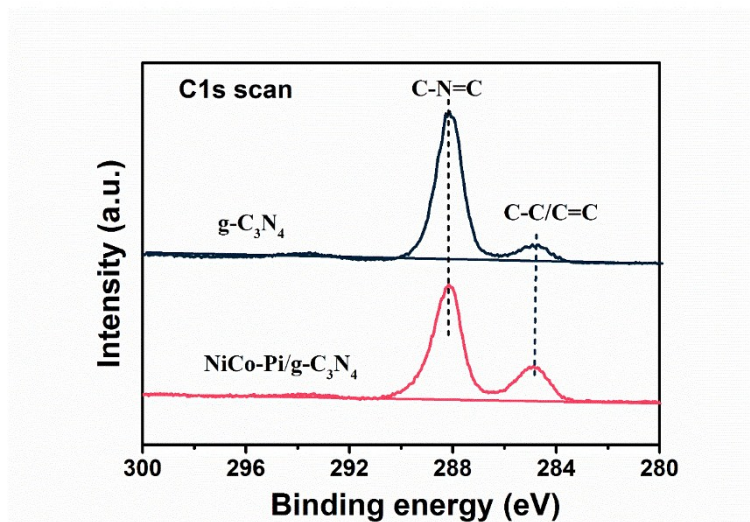


Fig. S8. C 1s XPS spectra of g-C₃N₄ and NiCo-Pi/g-C₃N₄. The C1s spectra can be differentiated into two peaks at 288.2 eV and 284.8 eV, which are ascribed to the C–N=C of the g-C₃N₄ and C–C/C=C groups, respectively.¹⁷

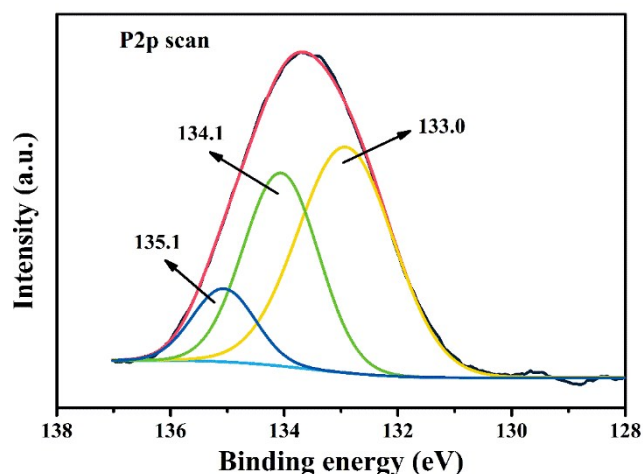


Fig. S9. P 2p XPS spectra of NiCo-Pi/g-C₃N₄.

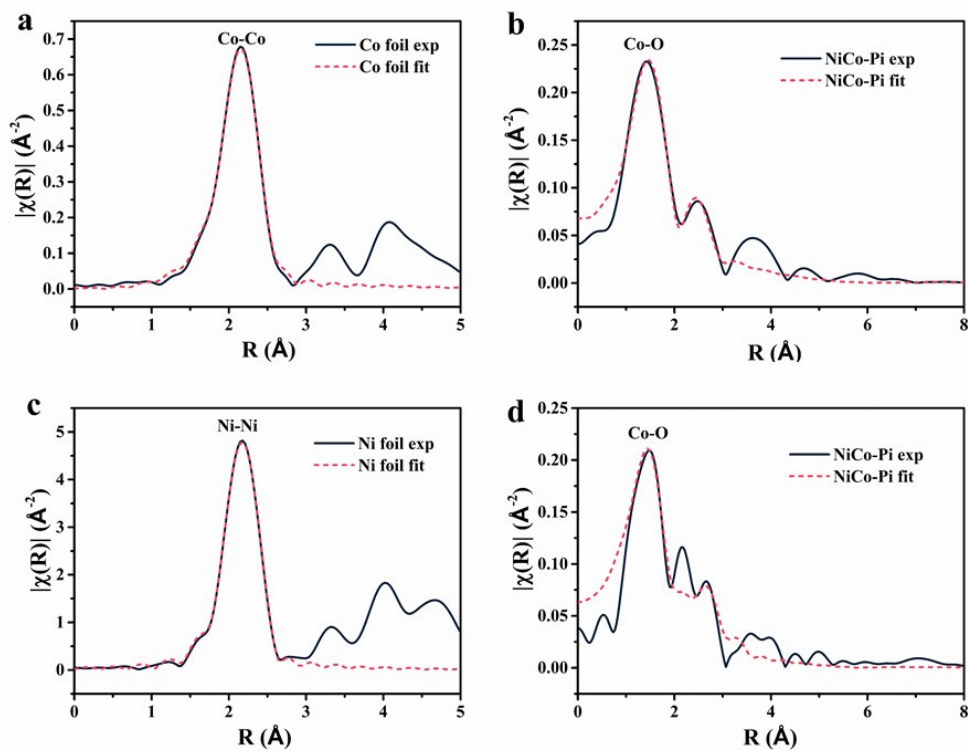


Fig. S10. Fourier transform magnitude of Co K-edge EXAFS spectra in R space for (a) Co foil, and (b) NiCo-Pi (not corrected for phase shift). Fourier transform magnitude of Ni K-edge EXAFS spectra in R space for (c) Ni foil, and (d) NiCo-Pi (not corrected for phase shift).

Table S3. Co K-edge EXAFS curve Fitting Parameters^[a]

Sample	shell	N	R (Å)	$\sigma^2 \times 10^{-3}$ (Å ²)	ΔE_0 (eV)	R factor
Co foil ^[b]	Co-Co	12	2.49	6.1	0.7	0.003
NiCo-Pi ^[c]	Co-O	4.6	2.05	10.9	-7.6	0.005
	Co-Co/Ni	2.7	3.01			
NiCo-Pi/g-C₃N₄ ^[d]	Co-N/O	6.0	2.05	10.1	-1.9	0.002
	Co-Co/Ni	1.9	3.01			

Table S4. Ni K-edge EXAFS curve Fitting Parameters^[a]

Sample	shell	N	R (Å)	$\sigma^2 \times 10^{-3}$ (Å ²)	ΔE_0 (eV)	R factor
Ni foil ^[e]	Ni-Ni	12	2.48	6.0	7.1	0.003
NiCo-Pi ^[f]	Ni-O	8.3	2.03	9.5	-8.4	0.003
	Ni-Co/Ni	3.4	3.46			
NiCo-Pi/g-C₃N₄ ^[g]	Ni-N/O	7.7	2.00	12.0	-11.7	0.018
	Ni-Co/Ni	5.7	3.42			

[a] N, coordination number; R, distance between absorber and backscatter atoms; σ^2 , Debye–Waller factor to account for both thermal and structural disorders; ΔE_0 , inner potential correction; R factor indicates the goodness of the fit. Error bounds (accuracies) that characterize the structural parameters obtained by EXAFS spectroscopy were estimated as $N \pm 20\%$; $R \pm 1\%$; $\sigma^2 \pm 20\%$; $\Delta E_0 \pm 20\%$. Bold numbers indicate a fixed coordination number (N) according to the crystal structure. [b] Fitting range: $3.0 \leq k$ (/Å) ≤ 12.5 and $1.0 \leq R$ (Å) ≤ 3.0 . [c] Fitting range: $3.0 \leq k$ (/Å) ≤ 8.0 and $1.0 \leq R$ (Å) ≤ 3.0 . [d] Fitting range: $3.0 \leq k$ (/Å) ≤ 8.0 and $1.0 \leq R$ (Å) ≤ 3.1 . [e] Fitting range: $3.0 \leq k$ (/Å) ≤ 12.5 and $1.0 \leq R$ (Å) ≤ 3.0 . [f] Fitting range: $3.0 \leq k$ (/Å) ≤ 10.0 and $1.0 \leq R$ (Å) ≤ 3.0 . [g] Fitting range: $3.0 \leq k$ (/Å) ≤ 10.0 and $1.0 \leq R$ (Å) ≤ 3.0 .

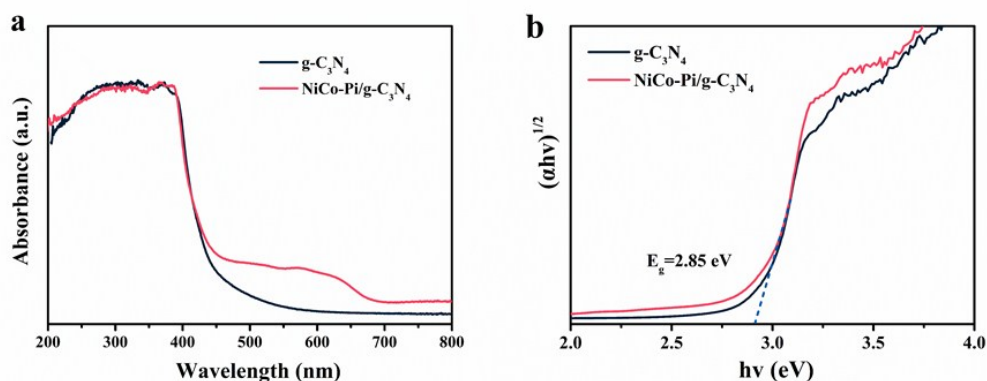


Fig. S11. (a) UV–visible adsorption spectra and (b) $(\alpha hv)^{1/2}$ versus $h\nu$ curves of $g\text{-C}_3\text{N}_4$ and $\text{NiCo-Pi/g-C}_3\text{N}_4$. Both samples exhibited the characteristic absorption at approximately 380 nm, which is assigned to $\pi\text{-}\pi^*$ transitions normally seen in heterocyclic aromatics of $g\text{-C}_3\text{N}_4$.¹⁸ The derived electronic band gaps of $g\text{-C}_3\text{N}_4$ and $\text{NiCo-Pi/g-C}_3\text{N}_4$ can be calculated according to the Tauc plots:

$$\alpha hv = A(h\nu - E_g)^{n/2}$$

where h is the Planck constant, ν is the light frequency, A is a constant, α is the absorption coefficient, and E_g is the band gap. The variable number n value of $g\text{-C}_3\text{N}_4$ is 1 due to its direct-allowed transition.^{19,20}

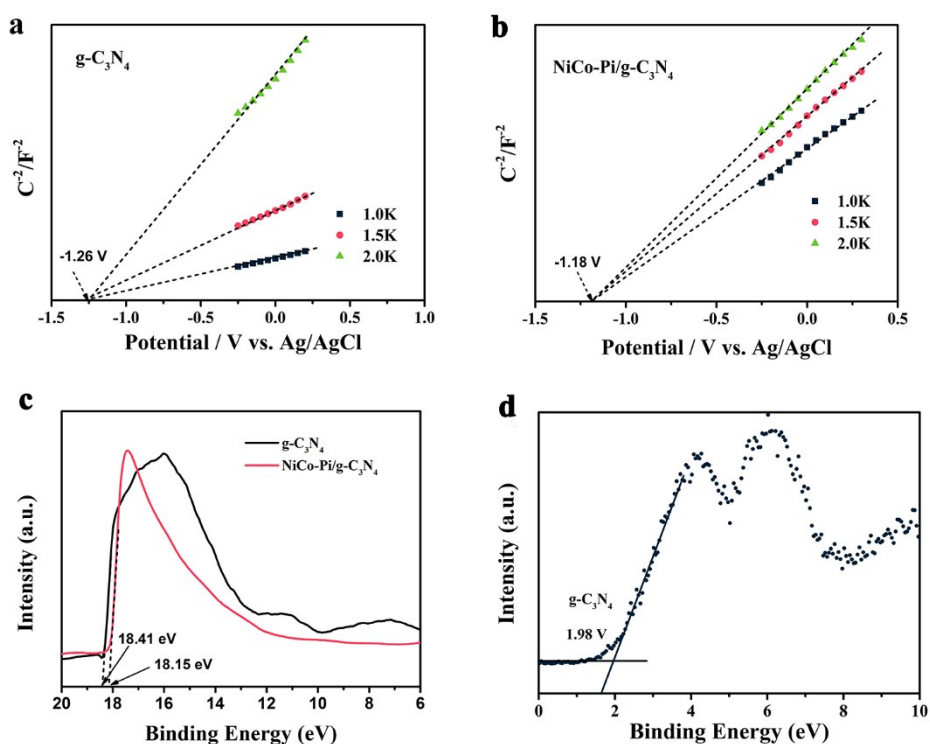


Fig. S12. (a) Mott-Schottky plots of $g\text{-C}_3\text{N}_4$, (b) $\text{NiCo-Pi/g-C}_3\text{N}_4$. (c) UPS spectra of $g\text{-C}_3\text{N}_4$ and $\text{NiCo-Pi/g-C}_3\text{N}_4$. (d) VB XPS of $g\text{-C}_3\text{N}_4$.

Table S5. Parameters of equivalent circuit for the impedance data of the prepared samples.

Sample	R_s (Ω)	R_{ct} ($k\Omega$)
$g-C_3N_4$	124	257
NiCo-Pi/ $g-C_3N_4$ (Ni:Co=0:1)	25.5	188
NiCo-Pi/ $g-C_3N_4$ (Ni:Co=1:3)	49.4	25.9
NiCo-Pi/ $g-C_3N_4$ (Ni:Co=2:3)	50	15
NiCo-Pi/ $g-C_3N_4$ (Ni:Co=4:5)	126	12.1
NiCo-Pi/ $g-C_3N_4$ (Ni:Co=1:1)	119	11.9
NiCo-Pi/ $g-C_3N_4$ (Ni:Co=0:1)	66.2	166

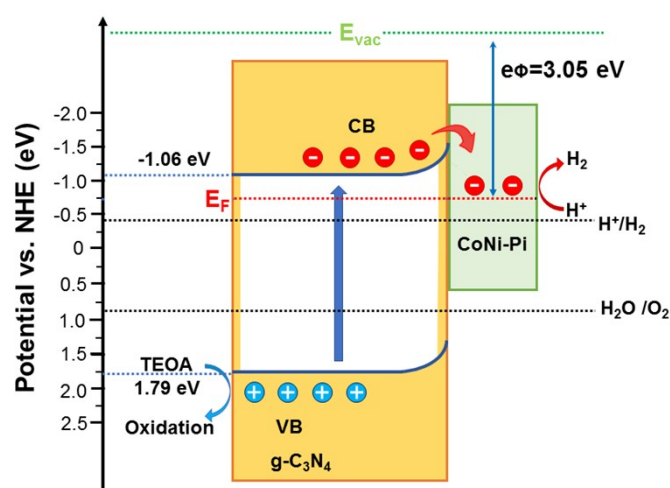


Fig. S13. Energy band configuration and photo-induced charge generation/transfer process in NiCo-Pi/ $g-C_3N_4$ during visible light photocatalytic H_2 evolution. E_F : Fermi level; E_{vac} : vacuum energy; $e\phi$: work functions

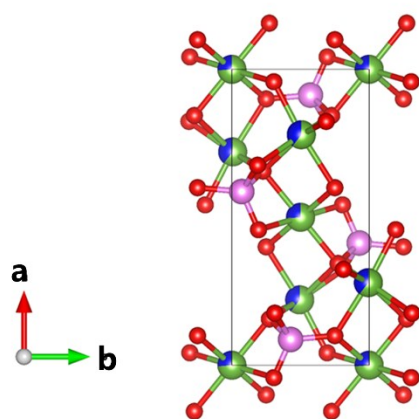


Fig. S14. The ball-and-stick model of $(\text{Ni}_{0.65}\text{Co}_{0.35})_3(\text{PO}_4)_2$. The $(\text{Ni}_{0.65}\text{Co}_{0.35})_3(\text{PO}_4)_2$ crystallized in the monoclinic system with the lattice constants $a= 10.185(4) \text{ \AA}$, $b= 4.713(3) \text{ \AA}$, $c= 5.865(2) \text{ \AA}$.²¹ The green, blue, red and violet balls represent Ni, Co, O, and P atoms, respectively. All the NiCo-Pi crystal structures with different Ni/Co molar ratios were geometrically optimized based on the above configuration.

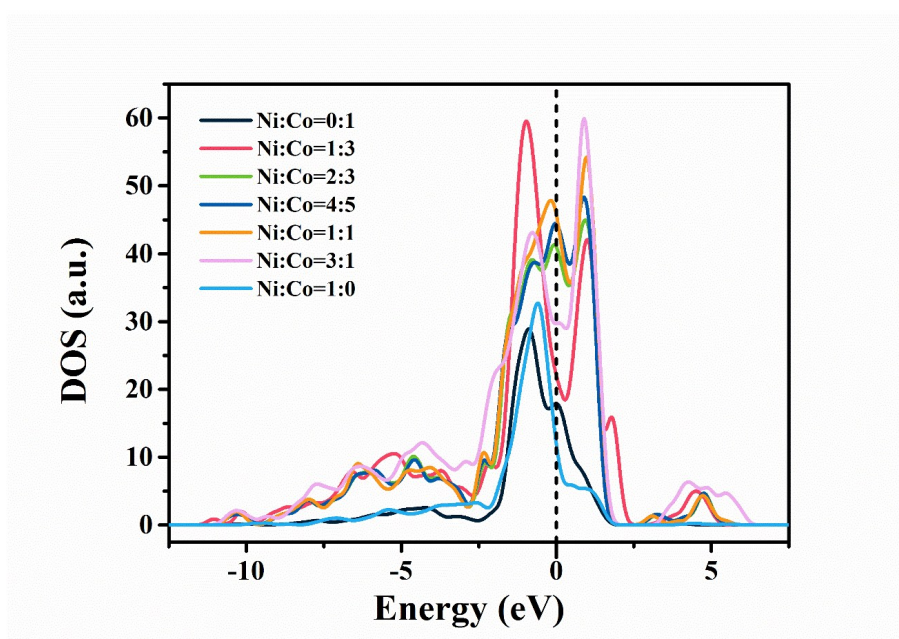


Fig. S15. d-band density of states for NiCo-Pi with different Ni/Co molar ratios. The black dashed line denotes the position of the Fermi level.

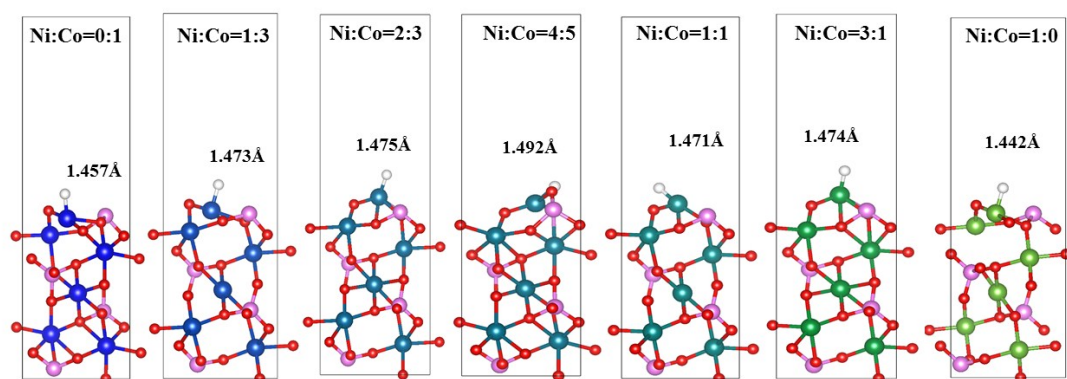


Fig. S16. Optimized geometry structures for H atom adsorption on surface of NiCo-Pi with different Ni/Co molar ratios. The white, red, violet and other colors represent H, O, P and Ni/Co atoms, respectively.

References

1. H. Zhang, P. Zhang, M. Qiu, J. Dong and X. W. Lou, *Adv. Mater.*, 2018, 1804883.
2. S. Kampouri, T. N. Nguyen, M. Spodaryk, R. G. Palgrave, A. Züttel, B. Smit and K. C. Stylianou, *Adv. Funct. Mater.*, 2018, **28**, 1806368.
3. K. Han, T. Kreuger, B. Mei and G. Mul, *ACS Catal.*, 2017, **7**, 1610-1614.
4. J. Dong, Y. Shi, C. Huang, Q. Wu, T. Zeng and W. Yao, *Appl. Catal., B* 2019, **243**, 27-35.
5. R. Boppella, W. Yang, J. Tan, H.-C. Kwon, J. Park and J. Moon, *Appl. Catal., B* 2019, **242**, 422-430.
6. X. Han, D. Xu, L. An, C. Hou, Y. Li, Q. Zhang and H. Wang, *Appl. Catal., B* 2019, **243**, 136-144.
7. J. Liu, Q. Jia, J. Long, X. Wang, Z. Gao and Q. Gu, *Appl. Catal., B* 2018, **222**, 35-43.
8. Y. Ping, X. Liu, J. Iocozzia, Y. P. Yuan, L. Gu, G. Xu and Z. Lin, *J. Mater. Chem. A*, 2017, **5**.
9. K. He, J. Xie, Z.-Q. Liu, N. Li, X. Chen, J. Hu and X. Li, *J. Mater. Chem. A*, 2018, **6**, 13110-13122.
10. C. Li, Y. Du, D. Wang, S. Yin, W. Tu, Z. Chen, M. Kraft, G. Chen and R. Xu, *Adv. Funct. Mater.*, 2017, **27**, 1604328.
11. J. Fu, C. Bie, B. Cheng, C. Jiang and J. Yu, *ACS Sustain. Chem. Eng.*, 2018, **6**, 2767-2779.
12. A. Indra, A. Acharjya, P. W. Menezes, C. Merschjann, D. Hollmann, M. Schwarze, M. Aktas, A. Friedrich, S. Lochbrunner, A. Thomas and M. Driess, *Angew. Chem. Int. Ed. Engl.*, 2017, **56**, 1653-1657.
13. Z. Qin, Y. Chen, Z. Huang, J. Su and L. Guo, *J. Mater. Chem. A*, 2017, **5**, 19025-19035.
14. J. Fu, B. Zhu, C. Jiang, B. Cheng, W. You and J. Yu, *Small*, 2017, **13**, 1603938.
15. R. Li, X. Zhu, X. Yan, H. Kobayashi, S. Yoshida, W. Chen, L. Du, K. Qian, B. Wu, S. Zou, L. Lu, W. Yi, Y. Zhou and J. Fan, *ACS Catal.*, 2017, **7**, 1478-1484.
16. L. Zhao, Q. Meng, X. Fan, C. Ye, X. Li, B. Chen, V. Ramamurthy, C. Tung, *Angew. Chem. Int. Ed. Engl.* 2017, **56**, 3020-3024.
17. K. Li, Y.-Z. Lin, Y. Zhang, M.-L. Xu, L.-W. Liu and F.-T. Liu, *J. Mater. Chem. C*, 2019, **7**, 13211-13217.
18. A. B. Jorge, D. J. Martin, M. T. S. Dhanoa, A. S. Rahman, N. Makwana, J. Tang, A. Sella, F. Corà, S. Firth, J. A. Darr and P. F. McMillan, *J. Phys. Chem. C*, 2013, **117**, 7178-7185.
19. H. Yu, R. Shi, Y. Zhao, T. Bian, Y. Zhao, C. Zhou, G. I. N. Waterhouse, L. Z. Wu, C. H. Tung and T. Zhang, *Adv. Mater.*, 2017, **29**, 1605148.
20. Q. Liang, Z. Li, Z.-H. Huang, F. Kang and Q.-H. Yang, *Adv. Funct. Mater.*, 2015, **25**, 6885-6892.
21. A. G. Nord, *Zeitschrift Für Kristallographie*, 1984, **166**, 159-176.